

TOSHIBA Diode Silicon Epitaxial Schottoky Barrier Type

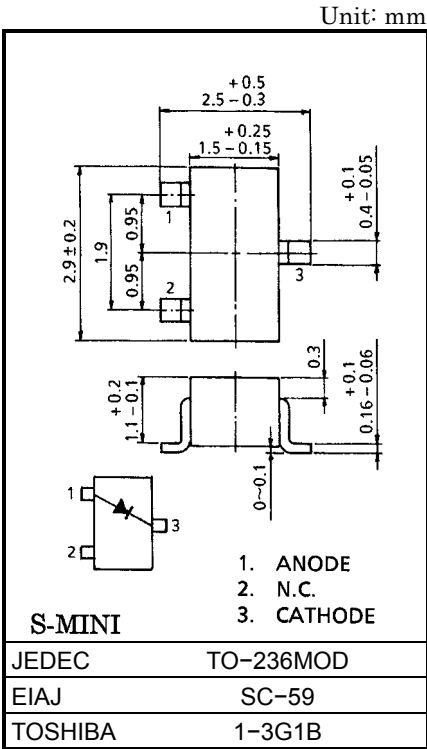
1SS294

Low Voltage High Speed Switching

- Low forward voltage : $V_F(3) = 0.54V$ (typ.)
- Low reverse current : $I_R = 5\mu A$ (max)
- Small package : SC-59

Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Maximum (peak) reverse voltage	V_{RM}	45	V
Reverse voltage	V_R	40	V
Maximum (peak) forward current	I_{FM}	300	mA
Average forward current	I_O	100	mA
Power dissipation	P	150	mW
Junction temperature	T_j	125	°C
Storage temperature range	T_{stg}	-55~125	°C



Weight: 0.012g

Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Forward voltage	$V_F(1)$	—	$I_F = 1mA$	—	0.28	—	V
	$V_F(2)$	—	$I_F = 10mA$	—	0.36	—	
	$V_F(3)$	—	$I_F = 100mA$	—	0.54	0.60	
Reverse current	I_R	—	$V_R = 40V$	—	—	5	μA
Total capacitance	C_T	—	$V_R = 0, f = 1MHz$	—	18	25	pF

Marking

